GANKIBAN: CN15MM

GaN Wafers

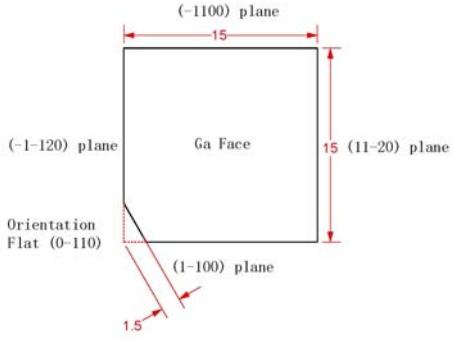
GaN wafers enable "GaN-on-GaN" structure of GaN-based optoelectronic and electronic devices such as blue/green laser diodes, light emitting diodes, high-power switching transistors, and RF transistors. GANKIBAN CN15MM is an n-type wafer produced by SixPoint's proprietary NEAT (near equilibrium ammonothermal) method. It is suitable for vertical devices including edge-emitting laser diodes, vertical high-power pn diodes and vertical high-power transistors.

Applications

R&D of GaN-based devices using homoepitaxy

Specifications

Wafer size	15 x 15 mm, with m-plane flat, usable area > 90%
Wafer thickness	300 ~ 400 micron
Orientation	C plane Miscut angle 0°+/-0.15° toward A, 0.4°+/-0.15° toward M
Surface finish	Ga-face --- CMP N-face --- as processed
XRD FWHM from (002)	< 100 arcsec (A-grade), < 200 arcsec (B-grade)
Conduction type	n-type (n > $1x10^{18}$ cm^{-3})



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